2N5460, 2N5461, 2N5462

JFET Amplifier

P-Channel – Depletion

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

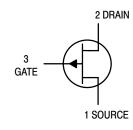
Rating	Symbol	Value	Unit
Drain – Gate Voltage	V _{DG}	40	Vdc
Reverse Gate – Source Voltage	V _{GSR}	40	Vdc
Forward Gate Current	I _{G(f)}	10	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	P _D	350 2.8	mW mW/°C
Junction Temperature Range	TJ	-65 to +135	°C
Storage Channel Temperature Range	T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



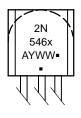
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MARKING DIAGRAM



2N546x	a = Device Code
	x = 0, 1, or 2
А	= Assembly Location
Y	= Year
WW	= Work Week
•	= Pb-Free Package
(Note: Microo	dot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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2N5460, 2N5461, 2N5462

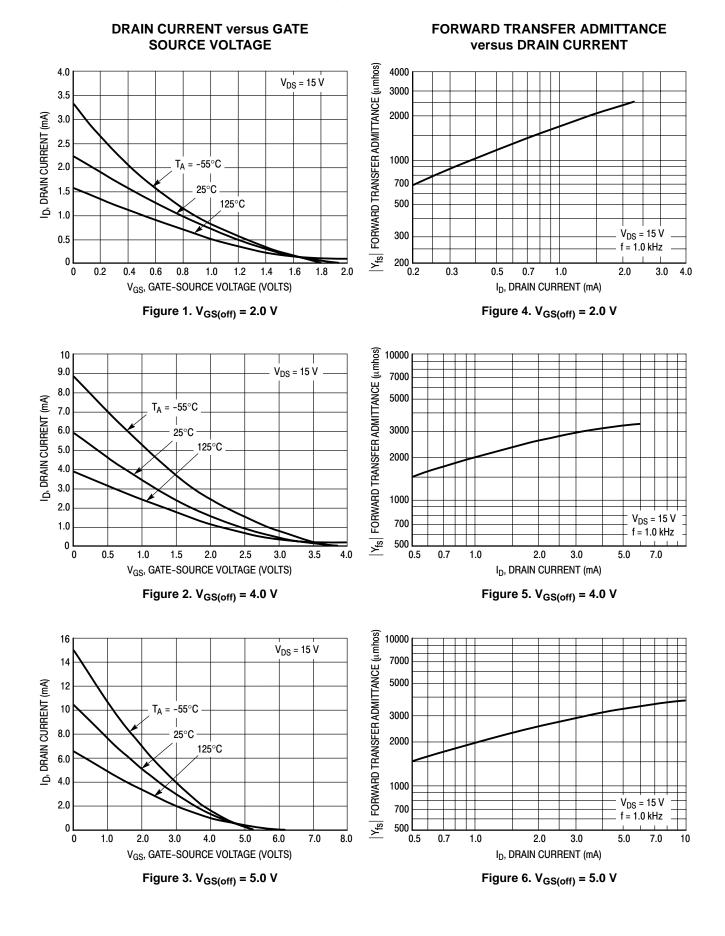
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Min Typ N	Max	Max Unit
OFF CHARACTERISTICS						
Gate – Source Breakdown Voltage ($I_G = 10 \ \mu Adc, \ V_{DS} = 0$)	2N5460, 2N5461, 2N5462	V _{(BR)GSS}	40	-	-	Vdc
Gate Reverse Current $(V_{GS} = 20 \text{ Vdc}, V_{DS} = 0)$ $(V_{GS} = 30 \text{ Vdc}, V_{DS} = 0)$	2N5460, 2N5461, 2N5462	I _{GSS}	_	_	5.0	nAdc
$(V_{GS} = 30 \text{ Vdc}, V_{DS} = 0)$ $(V_{GS} = 20 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C})$ $(V_{GS} = 30 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C})$	2N5460, 2N5461, 2N5462		-	-	1.0	μAdc
Gate – Source Cutoff Voltage $(V_{DS} = 15 \text{ Vdc}, I_D = 1.0 \mu \text{Adc})$	2N5460 2N5461 2N5462	V _{GS(off)}	0.75 1.0 1.8	- - -	6.0 7.5 9.0	Vdc
$ \begin{array}{l} \mbox{Gate} - \mbox{Source Voltage} \\ (V_{DS} = 15 \mbox{ Vdc}, \mbox{ I}_{D} = 0.1 \mbox{ mAdc}) \\ (V_{DS} = 15 \mbox{ Vdc}, \mbox{ I}_{D} = 0.2 \mbox{ mAdc}) \\ (V_{DS} = 15 \mbox{ Vdc}, \mbox{ I}_{D} = 0.4 \mbox{ mAdc}) \end{array} $	2N5460 2N5461 2N5462	V _{GS}	0.5 0.8 1.5	- - -	4.0 4.5 6.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	I _{DSS}	-1.0 -2.0 -4.0	- - -	-5.0 -9.0 -16	mAdc
SMALL-SIGNAL CHARACTERISTICS				4		.
Forward Transfer Admittance $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz})$	2N5460 2N5461 2N5462	y _{fs}	1000 1500 2000	- - -	4000 5000 6000	μmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f =	1.0 kHz)	y _{os}	-	-	75	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = $\frac{1}{2}$	1.0 MHz)	C _{iss}	-	5.0	7.0	pF
Reverse Transfer Capacitance (V _{DS} = 15 Vdc, V	/ _{GS} = 0, f = 1.0 MHz)	C _{rss}	-	1.0	2.0	pF
FUNCTIONAL CHARACTERISTICS						
Equivalent Short–Circuit Input Noise Voltage $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 100 \text{ Hz}, BW = 1$.0 Hz)	e _n	_	60	115	nV/\sqrt{Hz}

ORDERING INFORMATION

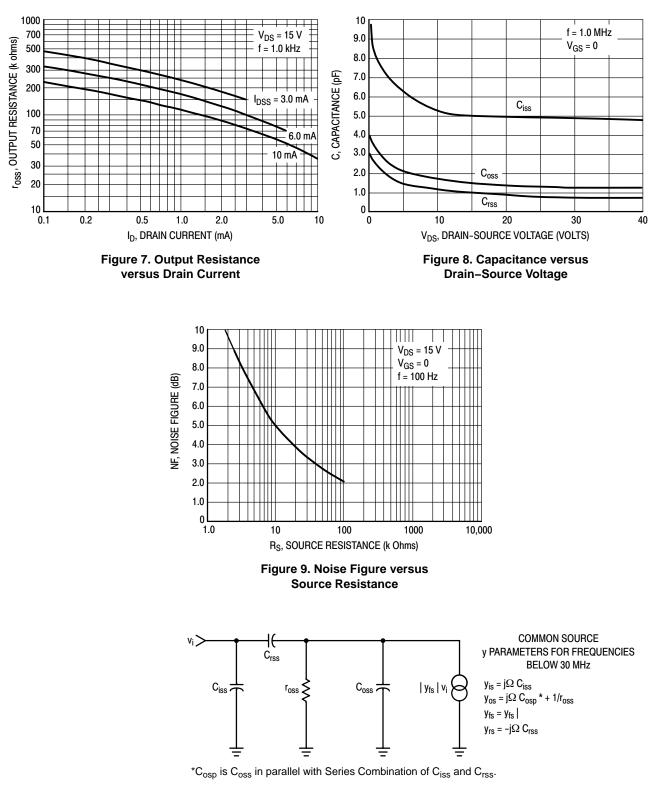
Device	Package	Shipping [†]
2N5460	TO-92	
2N5460G	TO-92 (Pb-Free)	1000 Haita / Davi
2N5461	TO-92	1000 Units / Box
2N5461G	TO-92 (Pb-Free)	
2N5461RLRA	TO-92	
2N5461RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N5462	TO-92	
2N5462G	TO-92 (Pb-Free)	1000 Units / Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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2N5460, 2N5461, 2N5462



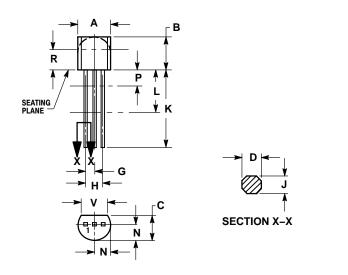
NOTE:

 Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).



PACKAGE DIMENSIONS

TO-92 CASE 29-11 ISSUE AL



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI V14 5M 1992

Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
L	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
Г	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

STYLE 7: PIN 1. SOURCE

2. DRAIN 3. GATE

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